

SE8016S

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

Thigh Density Cell Design For Ultra Low On-Resistance Fully Characterized Avalanche Voltage and Current Improved Shoot-Through FOM

- I Simple Drive Requirement
- I Small Package Outline
- I Surface Mount Device

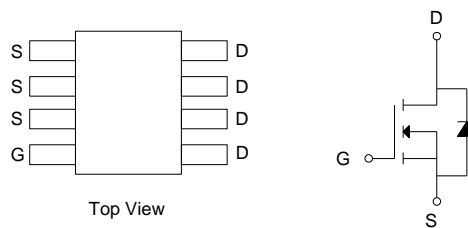
Features

For a single MOSFET

- I $V_{DS} = 80V$
- I $R_{DS(ON)} = 9m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



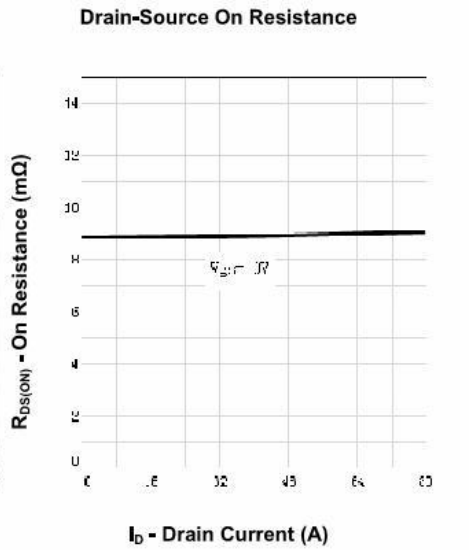
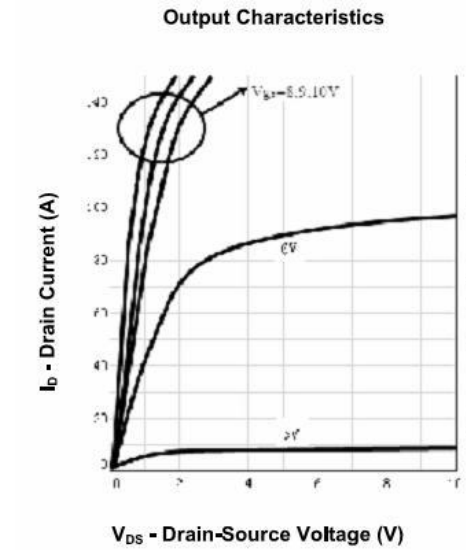
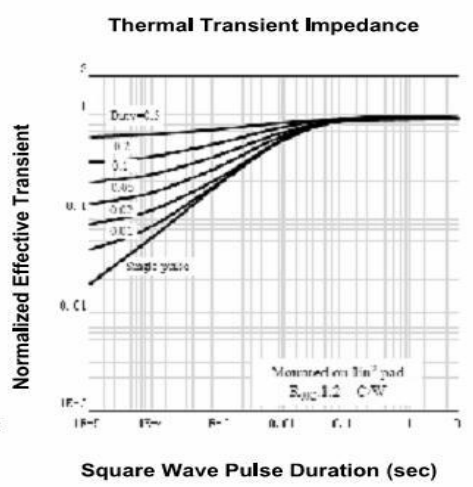
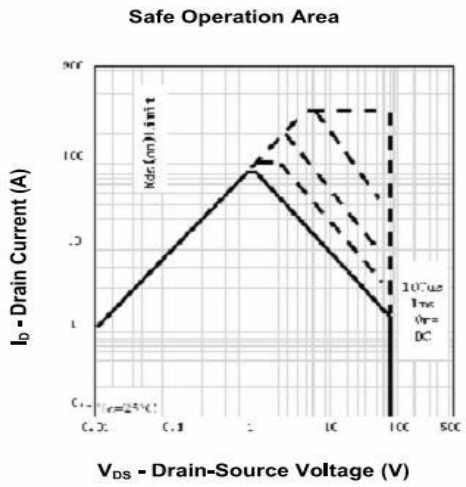
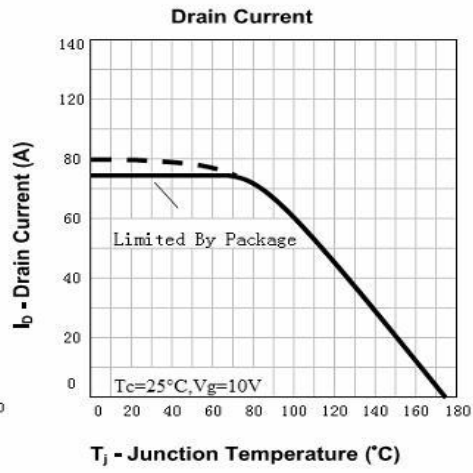
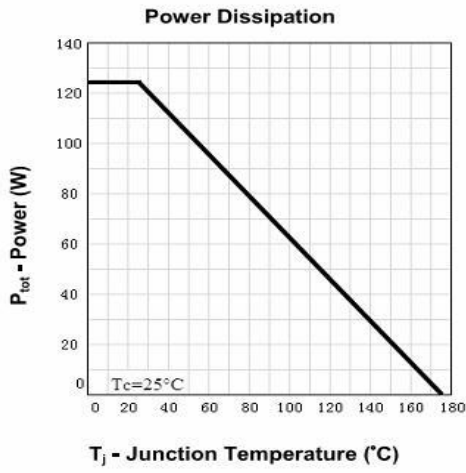
Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	80	A
	Pulsed		320	
Total Power Dissipation	@TA=25°C	P_D	125	W
Operating Junction Temperature Range		T_J	-55 to 175	°C

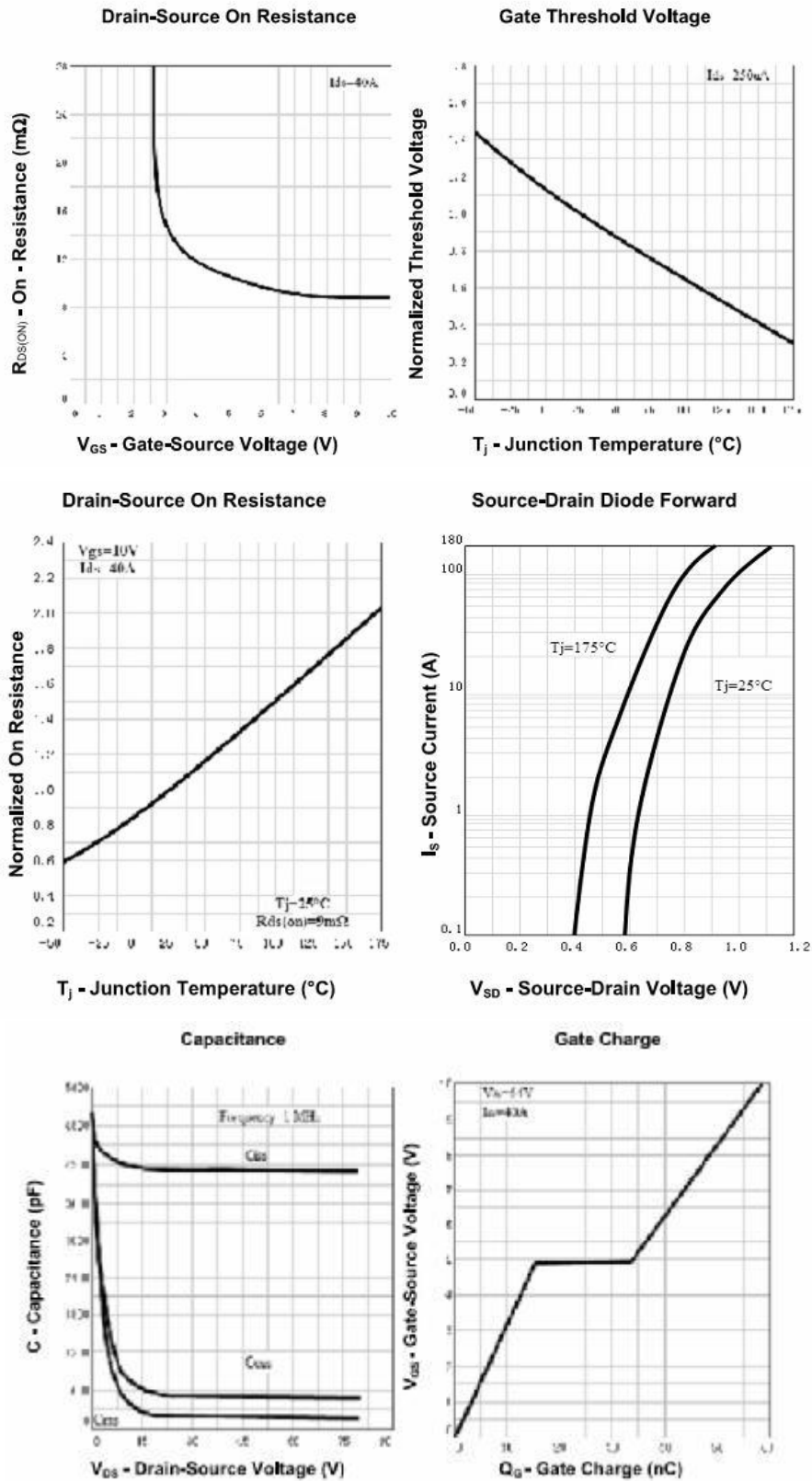
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Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	80			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 80V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =40A	-	9	11	mΩ
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =40V, f=1MHz		4020		pF
C _{oss}	Output Capacitance			510		pF
C _{rss}	Reverse Transfer Capacitance			201		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =64V, I _D =40A		58		nC
Q _{gs}	Gate Source Charge			15		nC
Q _{gd}	Gate Drain Charge			19		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =40V, R _{GEN} =4.7Ω I _D =2A		34		ns
t _{d(off)}	Turn-Off Delay Time			103		ns
t _{d(r)}	Turn-On Rise Time			95		ns
t _{d(f)}	Turn-Off Fall Time			33		ns
Thermal Resistance						
Symbol	Parameter	Typ	Max	Units		
R _{θJC}	Thermal Resistance Junction to Case(t≤10s)	-	1.2	°C/W		

Typical Characteristics



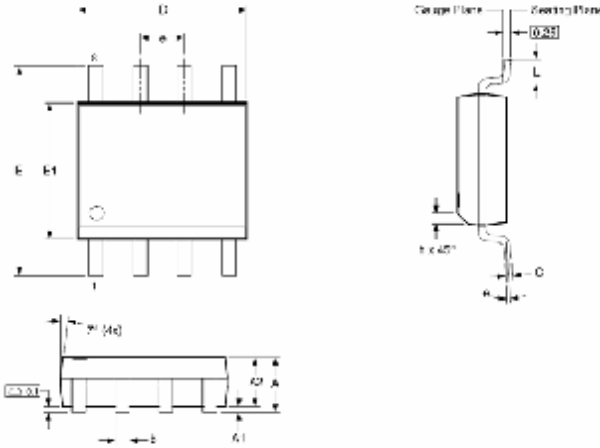
Typical Characteristics



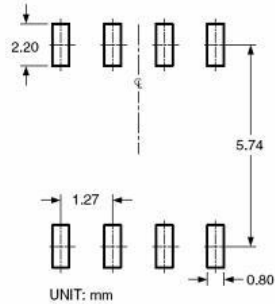
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Package Outline Dimension

SOP-8



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	1.35	1.65	1.75
A1	0.10	—	0.25
A2	1.25	1.50	1.65
b	0.31	—	0.51
c	0.17	—	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
e	1.27 BSC		
E	5.80	6.00	6.20
h	0.25	—	0.50
L	0.40	—	1.27
θ	0°	—	8°

Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.053	0.065	0.069
A1	0.004	—	0.010
A2	0.049	0.059	0.065
b	0.012	—	0.020
c	0.007	—	0.010
D	0.189	0.193	0.197
E1	0.150	0.154	0.157
e	0.050 BSC		
E	0.228	0.236	0.244
h	0.010	—	0.020
L	0.016	—	0.050
θ	0°	—	8°

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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